## Magnetic eld tuning of the low temperature state in Y bN iS i3

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## Abstract

W e present detailed, low tem perature, m agnetoresistance and speci c heat data of single crystal Y bN iSi<sub>3</sub> m easured in m agnetic eld applied along the easy m agnetic axis, H kb. An initially antiferrom agnetic ground state changes into a eld-induced m etam agnetic phase at 16 kO e (T ! 0). On further increase of m agnetic eld, m agnetic order is suppressed at 85 kO e. The functional behaviors of the resistivity and speci c heat are discussed in com parison with those of the few other stoichiom etric, heavy ferm ion com pounds with established eld-induced quantum critical point.

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The "quantum criticality conundrum "<sup>1</sup> continues to be a focus of attention for many theorists and experim entalists.<sup>2,3,4,5,6,7,8</sup> In the particular case of magnetic interm etallic com – pounds that manifest heavy ferm ion ground states, magnetic ordering tem peratures can be tuned by some control parameter to T = 0, bringing the material to a quantum critical point (QCP). This tuning is possible because of a delicate balance between the Ruderm an – K ittel – K asuya – Yoshida (RKKY) interaction, that de ness the magnetic ordering tem – perature, and the K ondo e ect, that causes screening of the magnetic moments and favors non-magnetic ground state.<sup>9</sup> Recently, in addition to traditionally used pressure and chem in cal substitution, magnetic eld has also emerged as a potential control parameter,<sup>2,6</sup> having an advantage of being a continuous and common parameter for a number of experimental techniques. However, the applicability of a single theoretical description for a QCP reached by using di erent tuning parameters, is still under discussion.

So far the number of stoichiom etric materials exhibiting a eld-induced QCP is rather small, with only few of them being Yb-based: YbRh<sub>2</sub>Si<sub>2</sub><sup>10</sup> YbAgGe<sup>11</sup> YbPtIn<sup>12</sup>. The release of entropy associated with the magnetic ordering (which can be used as a rough caliper of the size of the Y b m agnetic m om ent in the ordered state) in the three m aterials  $0.01R \ln 2$  for YbRh<sub>2</sub>Si<sub>2</sub>, to  $0.1R \ln 2$  for YbAgGe, to ranges from 0:6R ln 2 for Y bPtIn. Nevertheless the H T phase diagram s and functional behavior of a num ber of physical parameters in the vicinity of the eld-induced QCP are very similar for all three of these compounds. Recently investigated Y bN iSi,<sup>13</sup> an orthorhom bic, moderately - heavy ferm ion compound with the Neeltern perature,  $T_N = 5:1 \text{ K}$ , Som merfeld coe cient, 190 m J/m ol K<sup>2</sup>, and entropy associated with the magnetic ordering  $0.6R \ln 2$ , seem s to be a suitable candidate for further studies of the possible eld-induced quantum criticality in stoichiom etric, Yb-based, heavy ferm ions.

Single crystals of Y bN iSi<sub>b</sub> were grown from Sn ux (see Ref. 13 for m ore details). F lux residue from the surface of the sam ples was polished or/and etched out to exclude the e ect of elem ental Sn on m easured electrical transport properties. D C m agnetization was m easured up to 55 kO e and down to 1.8 K in a Q uantum D esign M PM S-5 SQ U ID m agnetom eter. H eat capacity and standard, 4-probe, AC (f = 16 H z) resistivity in zero and applied eld up to 140 kO e were m easured in a Q uantum D esign PPM S-14 instrum ent using a <sup>3</sup>H e refrigerator with heat capacity and ACT options respectively. In all measurem ents an external eld was applied along easy m agnetic axis (H kb).<sup>13</sup> R esistivity in applied eld was measured in a

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transverse, H ? I, con guration.

The low eld magnetic susceptibility, = M = H, measurements and 2 K magnetization, M (H), isotherms are consistent with the data reported in Ref. 13. The feature associated with the antiferrom agnetic transition in (or in d(T)=dT)<sup>14</sup> shifts to lower temperatures with increase of the magnetic eld applied (Fig. 1). The lower eld metamagnetic transition (Fig. 2) moves to lower elds with increase of temperature at which the M (H) data were taken, at higher temperatures the second feature moves to accessible eld range (upper left inset to Fig. 2); this feature corresponds to high eld break in M (H) slope reported previously<sup>13</sup>.

Field-dependent resistivity isotherm s are shown in Fig. 3. Two features (m arked with dashed lines), consistent with those seen in aforem entioned m agnetization (M (H)) m easurements, are easily recognizable and can be monitored in the H T dom ain of the experiments. The position of the lower eld feature is almost temperature-independent, while the critical eld associated with the higher eld feature decreases with an increase of temperature.

Representative-tem perature dependent resistivity, (T), curves are shown in Fig 4. No traces of the signal from residual Sn ux are seen in H = 0 data. The resistivity at base tem perature, T 400 mK, in zero eld is 2 cm, consistent with  $_0 = 1.5$  cm obtained from  $=_0 + AT^2$  t in [13]. A clear break of the (T) slope and the lower tem perature decrease of resistivity below the magnetic ordering tem perature,  $T_N$ , associated with a loss of spin-disorder scattering is observed up to 70 kO e. At higher elds no signature of magnetic transition can be seen. M oreover, there in no clear signature of traditional form of non-Ferm i-liquid behavior (linear or close-to-linear tem perature dependence of resistivity) at elds close to the one at which  $T_N$  is suppressed to T = 0 (Fig. 4, inset).

The tem perature-dependent heat capacity is shown in Fig. 5. Results in zero eld are consistent with the published data.<sup>13</sup> C onsistent to aforesaid, the peak in  $C_p$  (T) m oves down with an increase of the applied magnetic eld, it's height decreases, and it is not recognized in the data at 80 kO e and above. C beer exam ination of H = 70 kO e curve (Fig. 5b) reveals that the peak associated with the magnetic long range order is located on a background with a broad maximum. It is seen with m ore clarity if  $C_p$ =T is plotted as a function of tem perature (inset to Fig. 5b). This broad maximum m oves up in tem perature and acquires structure with an increase of applied eld: the data for H = 120 and 140 kO e can be deconvoluted to up to three broad peaks. For H 50 kO e these broad non-m onotonic background is

probably obscured by the feature in  $C_p$  (T) associated with the magnetic transition. The plausible explanation for these broad features is that they are Schottky-like contributions to the speci c heat: the the degeneracy of crystal-electric- eld-de ned lower energy levels of Y bN iSi<sub>2</sub> (e.g. a quadruplet or two closely spaced doublets) is lifted by the Zeem an term of the ham iltonian, and the energy di erence between di erent levels increases further on increase of the applied eld. This explanation is in in dispute with the assumption of the doublet ground state of Y bN iSi<sub>2</sub><sup>13</sup> and calls for additional studies.

In order to evaluate the change of the electronic speci c heat coe cient, , heat capacity data are re-plotted as  $C_p=T$  vs.  $T^2$  in Fig. 6. The small upturn at low tem peratures (left inset to Fig. 6) that becomes more pronounced at higher elds is probably associated with the nuclear Schottky contribution to the speci c heat. The Sommerfeld coe cient in the speci c heat, , can be estim ated by extrapolating the high tem perature linear part of the  $C_p=T$  vs.  $T^2$  curves to T = 0 (dashed line in Fig. 6). As a result of such procedure 250 m J/m ol K<sup>2</sup>, practically independent of the applied eld can be assessed. This value is close to the estimate in Ref. 13 for H = 0. However, this estimate exceeds signi cantly the values of  $C_p = T$  m easured in T ! 0 regime for magnetic elds in which the magnetic order is suppressed, pointing out that, at least for 70 kO e H 140 kOe, high tem perature extrapolation of  $C_p$ =T vs. T<sup>2</sup> is not an unique estimate of . This brings back the question of the estim ate of the entropy associated with the magnetic transition<sup>13</sup> and may point out that (in lieu of the data on non-m agnetic analogue) the non-m agnetic contribution, taken as extrapolation from above 10 K, was overestim ated and the cited value of S  $_{\rm m \ aq}$ 0:6R ln 2 was underestim ated.

Operationally, one can take the extrapolation to T ! 0 of the lowest temperature m easurements plotted as  $C_p=T$  vs.  $T^2$ , see left inset to Fig. 6 (ignoring the nuclear Schottky contribution), as an estimate of . The obtained values (right inset to Fig. 6) seem to follow the trend generally observed in materials close to  $Q C P^{10,11,12,15,16}$ . However, at least in the particular case of Y bN iSi<sub>b</sub>, one cannot discard the possibility that the shifts of the Schottky-like peaks to higher temperatures with an increase of the applied eld leads to a decreasing contribution (since it is taken further from the maximum) to the apparent =  $C_p=T$  j<sub>1</sub>, and genuine behavior of the Sommerfeld coe cient is masked by this fastly

changing contribution.

The therm odynam ic and transport m easurements on Y bN iSi<sub>3</sub> in m agnetic eld applied along the b-axis de ne the H T phase diagram (Fig. 7). This phase diagram is consistent (in overlapping H T domains) with the one recently suggested<sup>17</sup> from m agnetoresistance isotherms for T 1:85 K. The phase diagram is rather simple, with only two phases in the ordered state, and a triple point. The positions of the Schottky-like anomalies are also shown, depending on the applied eld in a close to linear fashion. A m agnetic eld of 85 kO e suppresses the long range order, m aking the phase diagram look similarly to the cases of eld-induced QCP recently discussed in several materials.<sup>10,11,12,15,16</sup> Further understanding of the low temperature state of Y bN iSi<sub>3</sub> in applied eld can be approached by detailed analysis of the m agnetotransport and therm odynam ic data.

Low temperature resistivity ((T)) data measured in magnetic eld were tted with the equation  $(T) = {}_{0} + AT$  (as e.g. in Ref. 18) with three tting parameters: residual resistivity, 0, pre-factor, A, and exponent, . Two sets of ts were perform ed: from 3 K down to base tem perature ( 0:4 K) and from 1.5 K down to base tem perature. Both sets of ts are giving similar results (Fig. 8). All three tting parameters have features associated with the critical elds, the lower critical eld being essentially temperature-independent below 3 K and the upper one only shifting slightly as T decreases from 3 K to 1.5 K (as can be seen in A and ). It is noteworthy that the exponent as calculated from the data above 0:4 K, does not fall below = 2, and the changes in as obtained from the 0.4 1.5 K are rather sm all (Fig. 8, upper panel). This is clearly di erent from the Κ Т case of eld-induced QCP in YbRh<sub>2</sub>Si<sub>2</sub>,  $^{10,15}$  YbAgG e<sup>11,18</sup> and other materials, although it is possible that approaches 1.0 for T < 0.4 K, and in a very narrow eld range.

In sum m ary, therm odynam ic and transport m easurem ents on Y bN iSi<sub>2</sub> (H kb) reveal H T phase diagram with two distinct, antiferrom agnetic and m etam agnetic, ordered phases and a triple point. An applied m agnetic eld of 85 kO e suppresses the m agnetic ordering tem perature. As distinct from several known heavy ferm ions with eld induced QCP, above 400 m K no non-Ferm i-signature in resistivity was observed in the vicinity of the critical eld for T 0:4 K, although they m ay well em erge for T < 0:4 K data. Heat capacity m easurem ents suggest that applied m agnetic eld splits degenerate ground state of Y bN iSi<sub>3</sub> and this eld-dependent split of the energy levels m anifest itself as Schottky-like anom alies. A dditionally, possible artifacts in assessing of the Som m erfeld coe cient from heat capacity

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m easurem ents, that have relevance beyond this particular com pound, were disclosed.

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FIG.1: Low temperature DC m agnetic susceptibility, M (T)=H, m easured in Y bN iSi<sub>3</sub> in di erent applied elds, H kb. Inset: d(T)=dT corresponding to the data in the main panel. G ap in the data near between 4.3 K and 4.6 K corresponds to the region of unstable temperature control in our M PM S-5 m agnetom eter.



FIG.2: Representative m agnetic isotherm s, M (H), m easured in Y bN iSi<sub>3</sub> at di erent tem peratures for H kb. Insets: enlarged low - and high - eld plots of corresponding dM =dH . A rrow s on upper left inset m ark second, high eld, feature, that broadens beyond resolution for T = 5 K.



FIG. 3: Low temperature resistivity isotherms, (H), measured at (from the bottom to the top) 0.4, 0.76, 1, 1.25, 1.5, 1.75, 2, 2.5, 3, and 4 K. Dashed lines are guide for the eye.



FIG. 4: Representative low temperature resistivity curves measured in zero and applied magnetic eld. Curves are shifted down along the Y-axis by multiplicative of 5 cm for clarity. Numbers correspond to applied eld in kOe.



FIG.5: Low temperature heat capacity,  $C_p$  (T), measured in dimensional magnetic elds. Inset to panel (b):  $C_p$ =T as a function of temperature. Note that the curve for H = 70 kO e is shown on both panels.



FIG.6: Heat capacity in applied eld for 70 kO e H 140 kO e plotted as  $C_p=T$  vs.  $T^2$ . D ashed line - linear extrapolation from the high tem perature data. Insets: left - enlarged low tem perature part; right - estimate of from extrapolated low tem perature linear portion of the  $C_p=T$  vs.  $T^2$  graph.



FIG. 7: Tentative H T phase diagram of Y bN iSi<sub>3</sub> for H jb. Dierent symbols correspond to the phase lines obtained from dierent therm odynamic and transport measurements: open circle -M (T), lled circle -M (H), open star -C<sub>p</sub>(T), lled star - (T), diamond and asterisk - (H). C rosses correspond to the position of broad maxima in C<sub>p</sub>=T, dashed lines are guides for the eye.



FIG. 8: Results of thing of low temperature resistivity to the form  $(T) = _0 + AT$ ; units of (T) and  $_0$  are cm.Circles: t from 3 K to the base temperature, triangles: t from 1.5 K to the base temperature. Nom inal error bars of the ts are shown. Vertical dashed lines m ark T ! 0 critical elds from the phase diagram above.